

HE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS:

Walter Fix et al.

SERIAL NO:

10/569,763

FILED:

February 23, 2006

EXAMINER

Not assigned

ART UNIT

Not assigned

FOR:

ORGANIC ELECTRONIC COMPONENT WITH HIGH

RESOLUTION STRUCTURING AND METHOD FOR THE

PRODUCTION THEREOF

ATTY DKT NO.:

411000-146

CUSTOMER NO.: 27162

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

DISCLOSURE STATEMENT UNDER 37 CFR 1.56

SIR:

This paper is to bring to the attention of the PTO the following commonly owned copending U.S. applications, all of which are related in different respects to organic electronic devices and/or method of making such devices such as transistors, diodes, integrated circuits and the like. Many of these applications also have one or more common inventors. The attached PTO 1449 lists these applications. It is respectfully requested that the Examiner consider and make of record all of the cited applications listed on the attached PTO 1449.

Application No.	<u>Title</u>	<u>Inventors</u>	Atty. Dkt. No.
10/344,951	Organic Field-Effect Transistor (OFET), A Production Method Therefor, An Integrated Circuit Constructed From the Same and Their Uses	Adolf Bernds et al.	411000-99
10/362,932	Organic Field Effect Transistor, Method for Structuring an OFET and Integrated Circuit	Adolf Bernds et al	411000-110

Receipt date: 05/03/2006

10/380,113	Organic Rectifier, Circuit, RFID Tag and Use of an Organic Rectifier	Adolf Bernds et al.	411000-106
10/381,032	Electrode and/or Conductor Track for Organic Components and Production Method Thereof	Adolf Bernds et al.	411000-105
10/433,959	Organic Field Effect Transistor, Method For Structuring an OFET and Integrated Circuit	Adolf Bernds	411000-108
10/433,961	Device For Detecting and/or Transmitting at Least One Environmental Influence, Method for Producing Said Device and Use Thereof	Wolfgang Clemens et al.	411000-111
10/467,636	Organic Field Effect Transistor With a Photostructured Gate Dielectric, Method for the Production and Use Thereof in Organic Electronics	Adolf Bernds et al.	411000-104
10/473,050	Device With At Least Two Organic Electronic Components and Method for Producing the Same	Adolf Bernds et al.	411000-113
10/479,234			411000-101
10/479,238	Method For Producing Conductive Structures by Means of Printing Technique, and Active Components Produced Therefrom For Integrated Circuits	Adolf Bernds et al.	411000-100
10/492,922	Insulator for An Organic Electronic Component	Erwann Guillet et al.	411000-115
10/492,923	Electronic Unit, Circuit Design for the Same and Production Method	Wolfgang Clemens et al.	411000-114
10/498,610	Organic Field Effect Transistor with Offset Threshold Voltage and the Use Thereof		411000-119
10/508,640	Logic Component Comprising Organic Field Effect Transistors	Walter Fix et al.	411000-120
10/508,737	Device and Method for Laser Structuring Functional Polymers and	Device and Method for Laser Structuring Adolf Bernds et al.	
10/517,750	Substrate for an Organic Field Effect Transistor, Use of the Substrate, Method of Increasing the Charge Carrier Mobility and Organic Field Effect Transistor (OFET)	Wolfgang Clemens et al.	411000-122
10/523,216	Electronic Component Comprising Predominantly Organic Functional Materials And A Process For The Production Thereof	Adolf Bernds et al.	411000-123
10/523,487	Electronic Device	Wolfgang Clemens et al.	411000-124
10/524,646	Organic Component for Overvoltage Protection and Associated Circuit	Walter Fix et al.	411000-127

10/533,756	Organic Electronic Component with High- Resolution Structuring and Process for the Production Thereof	Wolfgang Clemens et al.	411000-128
10/534,678	Measuring Apparatus for Determining an Analyte in a Liquid Sample	Wolfgang Clemens et al.	411000-129
10/535,448	Organic Electronic Component Comprising Semi-Conductive Functional Layer and Method for Producing Said Component	Wolfgang Clemens et al.	411000-131
10/535,449	Organic Electronic Component Comprising the Same Organic Material for at Least Two Functional Layers	Adolf Bernds et al.	411000-132
10/344,926	An Electronic Circuit Having an Encapsulated Organic-Electronic Component, and a Method for Making an Encapsulated Organic-Electronic Component	Wolfgang Clemens et al.	411000-133
10/541,815	Organo-Resistive Memory Unit	Axel Gerlt et al.	411000-136
10/541,956	Board or Substrate for an Organic Electronic Device and Use Thereof	Wolfgang Clemens et al.	411000-137
10/541,957	Organic Field Effect Transistor And Integrated Circuit	Walter Fix et al.	411000-138
10/543,561	Organic Storage Component and Corresponding Triggering Circuit	Wolfgang Clemens et al.	411000-139
10/542,678	Organic Electronic Component and Method For Producing Organic Electronic Devices	Adolf Bernds et al.	411000-140
10/542,679	Use of Conductive Carbon Black/Graphite Mixtures for the Production of Low-Cost Electronics	Adolf Bernds et al.	411000-141
10/562,989	Method and Device for Patterning Organic Layers	Jurgen Ficker	411000-143
10/562,869	Logic Gate With a Potential-Free Gage Electrode for Organic Integrated Circuits	Wolfram Glauert	411000-144
10/569,763	Organic Electronic Component With High Resolution Structuring And Method For The Production Thereof	Walter Fix	411000-146
10/568,730	Organic Capacitor With Voltage- Controlled Capacitance	Wolfgang Clemens	411000-147
10/569,233	Polymer mixtures for printed polymer electronic circuits	Adolf Bernds	411000-148
10/570,571	Mechanical Control Elements For Organic Polymer Electronic Devices	Wolfgang Clemens	411000-149

Receipt date: 05/03/2006 10569763 - GAU: 2895

The Commissioner is authorized to charge payment of any fees associated with this communication or credit any overpayment to Deposit Account No. 03-0678.

FIRST CLASS CERTIFICATE

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April 25, 2006

fanice Speidel Date

#287523

Respectfully submitted, Walter Fix et al.

by William Squire, Reg. No. 25,378

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Receipt date: 05/03/2006

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PTO/SB/08a (08-03) Approved for use through 07/31/2006. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. Department of Commerce ork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number

Substitute f	for form 1449A/PTO		Com	plete if Known
			Application Number	10/569,763
	INFORMATION DISC	LOSURE	Filing Date	February 23, 2006
·	STATEMENT BY APPLICANT		First Named Inventor	Walter Fix
			Group Art Unit	Notrassigned 2895
(Use as many sheets as necessary)		Examiner Name	Notassigmed J.García	
Sheet	1	2	Attorney Docket Number	411000-146

U.S. PATENT DOCUMENTS						
Cite No.1	Document Number Number-Kid Code ^{2 (if known)}	Publication- Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
133	US-10/344,926	02/12/2004	Adolf Bernds et al.	See Disclosure Statements filed		
99	US-10/344,951	02/12/2004	Adolf Bernds et al.			
106	US-10/380,113	09/25/2003	Adolf Bernds et al.			
105	US-10/381,032	02/12/2004	Adolf Bernds et al.			
108	US-10/433,959	04/01/2004	Adolf Bernds			
111	US-10/433,961	04/01/2004	Wolfgang Clemens et ai.			
109	US-10/451,108	05/13/2004	Mark Giles et al.			
104	US-10/467,636	11/04/2004	Adolf Bernds et al.			
113	US-10/473,050	05/20/2004	Adolf Bemds et al.			
101	US-10/479,234	12/30/2004	Adolf Bernds et al.			
100	US-10/479,238	10/20/2004	Adolf Bernds et al.			
115	US-10/492,922	03/03/2005	Erwann Buillet et al.			
114	US-10/492,923	12/23/2004	Wolfgang Clemens et al.			
119	US-10/498,610	09/29/2005	Walter Fix et al.			
120	US-10/508,640	12/15/2005	Walter Fix et al.			
121	US-10/508,737	05/19/2005	Adolf Bernds et al.			
122	US-10/517,750	10/13/2005	Wolfgang Clemens et al.			
123	US-10/523,216	02/02/2006	Adolf Bernds et al.			
124	US-10/523,487	N/A	Wolfgang Clemens et al.			
127	US-10/524,646	N/A	Walter Fix et al.			
128	US-10/533,756	N/A	Wolfgang Clemens et al.			
129	US-10/534,678	N/A	Wolfgang Clemens et al.			
131	US-10/535,448	N/A	W. Clemens et al.			
132	US-10/535,449	N/A	Walter Fix et al.			
	No.1 133 99 106 105 108 111 109 104 113 101 100 115 114 119 120 121 122 123 124 127 128 129 131	No.1 Number-Kid Code ^{2 (f krown)} 133 US-10/344,926 99 US-10/380,113 105 US-10/381,032 108 US-10/433,959 111 US-10/451,108 109 US-10/451,108 104 US-10/467,636 113 US-10/479,234 100 US-10/479,234 100 US-10/479,238 115 US-10/492,922 114 US-10/498,610 120 US-10/508,640 121 US-10/508,737 122 US-10/508,737 122 US-10/523,216 124 US-10/523,487 127 US-10/523,487 128 US-10/533,756 129 US-10/535,448	Cite No.¹ Document Number Publication- Date MM-DD-YYYY 133 US-10/344,926 02/12/2004 99 US-10/344,951 02/12/2004 106 US-10/380,113 09/25/2003 105 US-10/381,032 02/12/2004 108 US-10/433,959 04/01/2004 111 US-10/433,959 04/01/2004 109 US-10/433,961 05/13/2004 109 US-10/451,108 05/13/2004 101 US-10/467,636 11/04/2004 113 US-10/479,234 12/30/2004 101 US-10/479,234 12/30/2004 100 US-10/479,238 10/20/2004 115 US-10/492,923 12/23/2004 119 US-10/492,923 12/23/2004 119 US-10/498,610 09/29/2005 120 US-10/508,737 05/19/2005 121 US-10/508,737 05/19/2005 122 US-10/523,216 02/02/2006 124 US-10/523,487 N/A 127 US-1	Cite No.1 Document Number Number Publication- Date MM-DD-YYYY Name of Patentee or Applicant of Cited Document 133 US-10/344,926 02/12/2004 Adolf Bernds et al. 99 US-10/344,951 02/12/2004 Adolf Bernds et al. 106 US-10/380,113 09/25/2003 Adolf Bernds et al. 105 US-10/381,032 02/12/2004 Adolf Bernds et al. 108 US-10/433,959 04/01/2004 Adolf Bernds 111 US-10/433,961 04/01/2004 Wolfgang Clemens et al. 109 US-10/451,108 05/13/2004 Mark Giles et al. 104 US-10/467,636 11/04/2004 Adolf Bernds et al. 113 US-10/479,234 12/30/2004 Adolf Bernds et al. 101 US-10/479,238 10/20/2004 Adolf Bernds et al. 115 US-10/492,923 12/23/2004 Wolfgang Clemens et al. 119 US-10/498,610 09/29/2005 Walter Fix et al. 120 US-10/508,640 12/15/2005 Walter Fix et al. 121 US-10/508,737 05/19/2005 </td		

Receipt date: 05/03/2006 10569763 - GAU: 2895

133	US-10/344,926	02/12/2004	Adolf Berr	ade et al	
133	03-10/344,920	02/12/2004	Adoli Beli	ius et ai.	
136	US-10/541,815	N/A	Axel Gerit	et al.	
137	US-10/541,956	N/A	Wolfgang	Clemens et al.	
138	US10/541,957	N/A	Walter Fix	c et al.	
139	US-10/543,561	N/A	Wolfgang	Clemens et al.	
140	US-10/542,678	N/A	Adolf Ben	nds et al.	,
141	US-10/542,679	N/A	Adolf Ben	nds et al.	
143	US-10/562,989	N/A	Jurgen Fi	cker et al.	
144	US-10/562,869	N/A	Wolfram	Glauert	
146	US-10/569,763	N/A	Walter Fix	c et al.	
147	US-10/568,730	N/A	Wolfgang	Clemens et al.	
148	US-10/569,233	N/A	Adolf Ben	nds et al.	
149	US-10/570,571	N/A	Clemens	et al.	
Examiner Signature	/Joannie Garcia/			Date Considered	10/10/2008

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional). See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. Applicant is to place a check mark here if English language Translation is attached. This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. Do NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.

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APPLICATION OF:

Walter Fix et al.

SERIAL NO:

10/569,763

GROUP ART UNIT:

Not assigned

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EXAMINER:

Not

assigned

CUSTOMER NO.:

27162

FOR:

ORGANIC ELECTRONIC COMPONENT WITH HIGH

RESOLUTION STRUCTURING AND METHOD FOR THE

PRODUCTION THEREOF

ATTY/DKT NO.:

411000-146

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

SIR:

Pursuant to 37 C.F.R. §1.56(a), Applicant(s) hereby cite(s) the enclosed documents listed on the attached copy of Form PTO-1449. Applicant(s) make no admission that the cited references are prior art or that these references are in fact material to the patentability of the above-entitled application.

This Information Disclosure Statement is filed in accordance with the paragraph of 37 CFR §1.97 indicated below:

_X__§1.97(b)

This Information Disclosure Statement is filed:

- (1) Within three months of the filing date of a national application; OR
- (2) Within three months of the date of entry of the national stage of an international application; OR
- (3) Before the mailing of a first Office Action on the merits. No fee or statement is required.

Receipt date: 05/03/2006 10569763 - GAU: 2895

§1.97(c)		paragraph (b) above, but before the mailing date of
	(1) (2)	A Final Action or under 37 CFR §1.113; OR A Notice of Allowance under 37 CFR §1.311; AND
	is acc	ompanied by either: (check one) The statement as specified in 37 CFR §1.97(e) set out below; OR The fee of \$180.00 under 37 CFR §1.17(p).
§1.97(d)	This Informa of eith	tion Disclosure Statement is filed after the mailing date
	(1) (2)	a Final Action or under 37 CFR §1.113; OR A Notice of Allowance under 37 CFR §1.311;
		or before payment of the Issue Fee; AND
		ompanied by:
	(1)	The statement as specified in 37 CFR §1.97(e) as set forth below; AND
	(2)	Petition is hereby made under 37 CFR §1.97(d) for consideration of this Information Disclosure Statement; AND,
	(3)	The petition fee of \$180.00 set out in 37 CFR §1.17(i).
§1.97(e)	The undersig	ned Attorney hereby states that:
	Statement wo	of information contained in this Information Disclosure as first cited in any communication from a foreign patent unterpart foreign application not more than three months ing date of this Information Disclosure Statement;
	no item of Statement w in a counte undersigned any individu	information contained in this Information Disclosure as cited in a communication from a foreign patent office rpart foreign application, or to the knowledge of the Attorney after making reasonable inquiry, was known to all designated in 37 CFR §1.56(c) more than three or to the filing date of the Information Disclosure

The relevancy of the cited foreign language documents in the attached Form 1449 is that these were cited in one or more of foreign counterparts of the co-pending, commonly owned U.S. applications listed in the attached Disclosure Statement.

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Janice Speidel

April 25, 2006

Date

#287505

Respectfully submitted, Walter Fix et al,

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U.S. Patent and Trademark Office; U.S. Department of Commerce lisplays a valid OMB control number.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number Substitute for form 1449A/PTO Complete if Known Application Number 10/569,763 INFORMATION DISCLOSURE Filing Date Feb. 23, 2006 STATEMENT BY APPLICANT MAY 0 3 2006 First Named Inventor Walter Fix · 2 2006 2895 Group Art Unit Not-seeigned (Use as many sheets as necessary) Net-sesigned J. Garcia **Examiner Name** Of 13 Attorney Docket Number 411000-146

U.S. PATENT DOCUMENTS					
Examiner Initial*	Cite No. ¹	Document Number Number-Kid Code ^{2 (if known)}	Publication- Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages o Relevant Figures Appear
		US-2002/0022284	02-21-2002	Heeger	
		US-2002/0053320	05-09-2002	Duthaler	
		US-2002/0056839	05-16-2002	Joo et al.	
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		US-3,512,052	12-12-1970	MacIver et al.	
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		US-4,246,298	01-20-1981	Guarnery	
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		US-4,340,057	07-20-1982	Bloch	
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		US-4,554,229	11-19-1985	Small	
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Substitute	for form 1449A/PT	49A/PTO <i>Comp</i>			plete if Kn	own	
				Application Number		10/569,76	3
	INFO	RMATION DISCLO	DSURE	Filing Date Feb. 23, 2006			006
	STAT	EMENT BY APPL	ICANT	Firs	t Named Inventor	Walter Fix	
				Gro	up Art Unit	Net-essign	red 2895
	(Use	as many sheets as nece	essary)	Exa	Examiner Name	Not assign	red J.Garci
Sheet	2		13	Atto	orney Docket Number	411000-14	16
		US-4,937,119	06-26-1990		Nickles et al.		
		US-5,075,816	12-24-1991		Stormbom		
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Maegawa

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Allen

Jain

Shi

Smayling

Aratani

Sakata et al.

Kondo et al.

Birch et al.

Isoda et al.

Tanaka et al.

Dimitrakopoulos

Allen

Receipt date: 05/03/2006

Substitute for form 1449A/PTO Complete if Known **Application Number** 10/569,763 INFORMATION DISCLOSURE Filing Date Feb. 23, 2006 STATEMENT BY APPLICANT First Named Inventor Walter Fix 2895 Group Art Unit Net-assigned Not cooligned J. Garcia (Use as many sheets as necessary) **Examiner Name** 3 Sheet 13 Attorney Docket Number 411000-146

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Valter Fix	
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			Group Art Unit	Net-assigned 2895	
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT			Application Number	10/569,763	
			Filing Date	Feb. 23, 2006 Walter Fix	
			First Named Inventor		
			Group Art Unit	Not-assigned 2895	
(Use as many sheets as necessary)			Examiner Name	Not-cooligned J. Garcia	
Sheet	13	13	Attorney Docket Number	411000-146	

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